



IFW

AMENDMENT TRANSMITTAL LETTER

Docket No.
FIS920030199US1

Application No.
10/604,607

Filing Date
August 4, 2003

Examiner
Thanh T. Nguyen

Art Unit
2813

Applicant(s): **Huajie Chen et al.**

STRUCTURE AND METHOD OF MAKING STRAINED SEMICONDUCTOR CMOS
Invention: **TRANSISTORS HAVING LATTICE-MISMATCHED SEMICONDUCTOR REGIONS**
UNDERLYING SOURCE AND DRAIN REGIONS (As Amended)

TO THE COMMISSIONER FOR PATENTS

Transmitted herewith is an amendment in the above-identified application.

The fee has been calculated and is transmitted as shown below.

CLAIMS AS AMENDED

| | Claims Remaining After Amendment | Highest Number Previously Paid | Number Extra Claims Present | Rate | |
|--|---|---|-----------------------------------|------|--|
| Total Claims | 31 | 32 | 0 | | |
| Independent Claims | 3 | - 3 | 0 | | |
| Multiple Dependent Claims (check if applicable) <input type="checkbox"/> | | | | | |
| Other fee (please specify): | | | | | |
| TOTAL ADDITIONAL FEE FOR THIS AMENDMENT: | | | | | |

☒ Large Entity

☐ Small Entity

☒ No additional fee is required for this amendment.

☐ Please charge Deposit Account No. _____ in the amount of \$ _____
A duplicate copy of this sheet is enclosed.

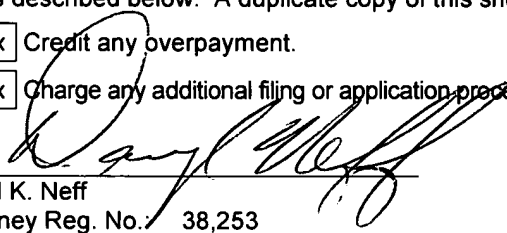
☐ A check in the amount of \$ _____ to cover the filing fee is enclosed.

☐ Payment by credit card. Form PTO-2038 is attached.

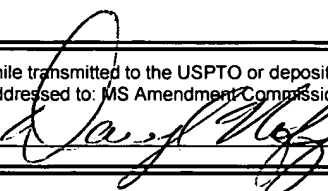
☒ The Director is hereby authorized to charge and credit Deposit Account No. **09-0458**
as described below. A duplicate copy of this sheet is enclosed.

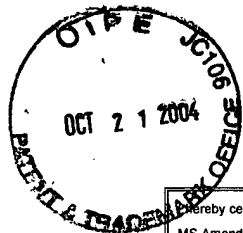
☒ Credit any overpayment.

☒ Charge any additional filing or application processing fees required under 37 CFR 1.16 and 1.17.


Daryl K. Neff
Attorney Reg. No.: 38,253

Dated: October 18, 2004

I hereby certify that this correspondence is being facsimile transmitted to the USPTO or deposited with the U.S. Postal Service with sufficient postage as First Class Mail, in an envelope addressed to: MS Amendment Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on the date shown below.
Dated: October 18, 2004
Signature:  (Daryl K. Neff)



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MS Amendment, Commissioner for Patents, Alexandria, VA 22313-1450 on this date: October 18, 2004

Name of Depositor:

Daryl K. Neff

Signature & Date

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

| | |
|--|---|
| In re application of: Huajie Chen, et al. | Date: October 18, 2004 |
| Serial Number: 10/604,607 | Examiner: Thanh T. Nguyen |
| Filed: August 4, 2003 | Group Art Unit: 2813 |
| Title: STRUCTURE AND METHOD OF MAKING STRAINED SEMICONDUCTOR CMOS TRANSISTORS HAVING LATTICE- MISMATCHED SEMICONDUCTOR REGIONS UNDERLYING SOURCE AND DRAIN REGIONS (As Amended) | H. Daniel Schnurmann IBM Corporation D/18G, B/300, Zip 482 2070 Route 52 Hopewell Junction, NY 12533-6531 |

AMENDMENT

MS Amendment
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

In response to the Office Action dated July 16, 2004, Applicants submit the following amendments and remarks for the Examiner's consideration.

Title of Invention:

Please amend the title to read:

STRUCTURE AND METHOD OF MAKING STRAINED SEMICONDUCTOR CMOS
TRANSISTORS HAVING LATTICE-MISMATCHED SEMICONDUCTOR REGIONS
UNDERLYING SOURCE AND DRAIN REGIONS